



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

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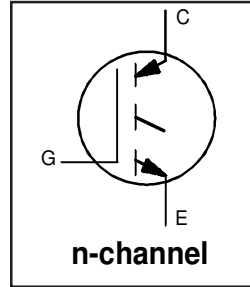
Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Features

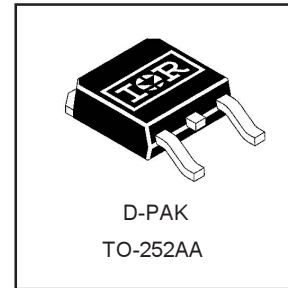
- Short Circuit Rated UltraFast: Optimized for high operating frequencies >5.0 kHz , and Short Circuit Rated to 10 μ s @ 125°C, V_{GE} = 15V
- Generation 4 IGBT design provides higher efficiency than Generation 3
- Industry standard TO-252AA package
- Lead-Free



V _{CES} = 600V
V _{CE(on)} typ. = 2.39V
@V _{GE} = 15V, I _C = 5.0A

Benefits

- Generation 4 IGBT's offer highest efficiency available
- IGBT's optimized for specified application conditions



Absolute Maximum Ratings

	Parameter	Max.	Units
V _{CES}	Collector-to-Emitter Breakdown Voltage	600	V
I _C @ T _C = 25°C	Continuous Collector Current	9.0	A
I _C @ T _C = 100°C	Continuous Collector Current	5.0	
I _{CM}	Pulsed Collector Current ①	18	
I _{LM}	Clamped Inductive Load Current ②	18	
t _{sc}	Short Circuit Withstand Time	10	μ s
V _{GE}	Gate-to-Emitter Voltage	\pm 20	V
E _{ARV}	Reverse Voltage Avalanche Energy ③	34	mJ
P _D @ T _C = 25°C	Maximum Power Dissipation	38	W
P _D @ T _C = 100°C	Maximum Power Dissipation	15	
T _J	Operating Junction and	-55 to + 150	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm) from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	3.3	°C/W
R _{θJA}	Junction-to-Ambient (PCB mount)*	—	50	
Wt	Weight	0.3 (0.01)	—	g (oz)

* When mounted on 1" square PCB (FR-4 or G-10 Material).
 For recommended footprint and soldering techniques refer to application note #AN-994
www.irf.com

IRG4RC10KPbF

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ①	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.58	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	2.39	2.62	V	$I_C = 5.0A$ $V_{GE} = 15V$ See Fig.2, 5
		—	3.25	—		
		—	2.63	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ②	1.2	1.8	—	S	$V_{CE} = 50V, I_C = 5.0A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	19	29	nC	$I_C = 5.0A$ $V_{CC} = 400V$ See Fig.8 $V_{GE} = 15V$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	2.9	4.3		
Q_{gc}	Gate - Collector Charge (turn-on)	—	9.8	15		
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 5.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 100\Omega$ Energy losses include "tail" See Fig. 9,10,14
t_r	Rise Time	—	24	—		
$t_{d(off)}$	Turn-Off Delay Time	—	51	77		
t_f	Fall Time	—	190	290		
E_{on}	Turn-On Switching Loss	—	0.16	—		
E_{off}	Turn-Off Switching Loss	—	0.10	—	mJ	See Fig. 9,10,14
E_{ts}	Total Switching Loss	—	0.26	0.32		
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	$V_{CC} = 400V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 100\Omega, V_{CPK} < 500V$
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$T_J = 150^\circ\text{C}$, $I_C = 5.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 100\Omega$ Energy losses include "tail" See Fig. 10,11,14
t_r	Rise Time	—	27	—		
$t_{d(off)}$	Turn-Off Delay Time	—	67	—		
t_f	Fall Time	—	350	—		
E_{ts}	Total Switching Loss	—	0.47	—		
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	220	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$
C_{oes}	Output Capacitance	—	29	—		
C_{res}	Reverse Transfer Capacitance	—	7.5	—		

Notes:

- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC} = 80\%(V_{CES}), V_{GE} = 20V, L = 10\mu H, R_G = 100\Omega$, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

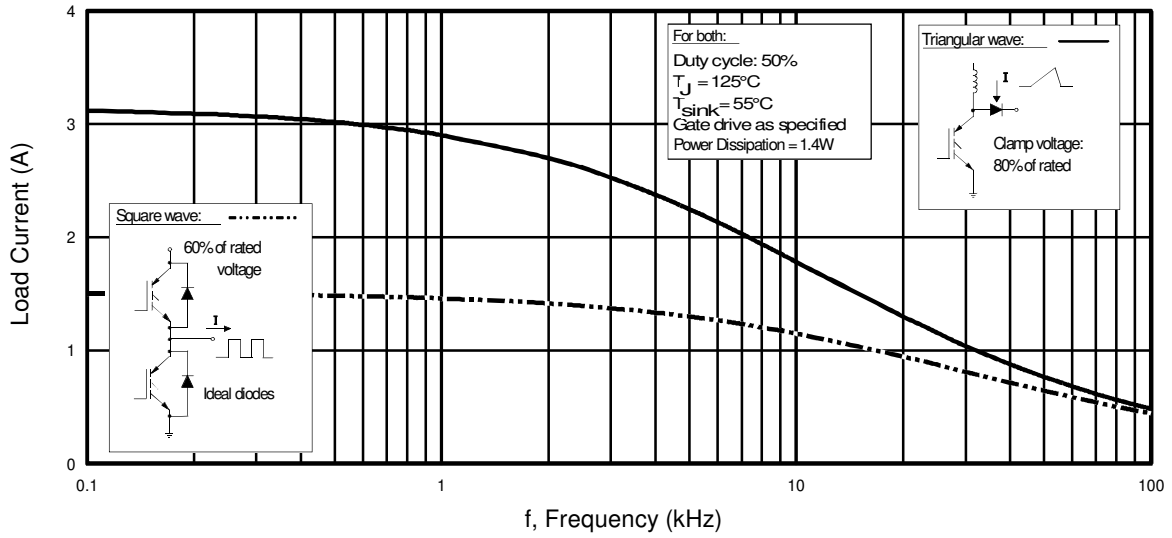


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

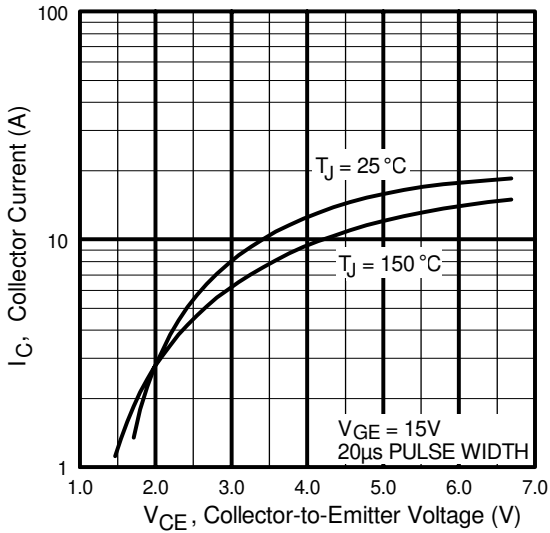


Fig. 2 - Typical Output Characteristics

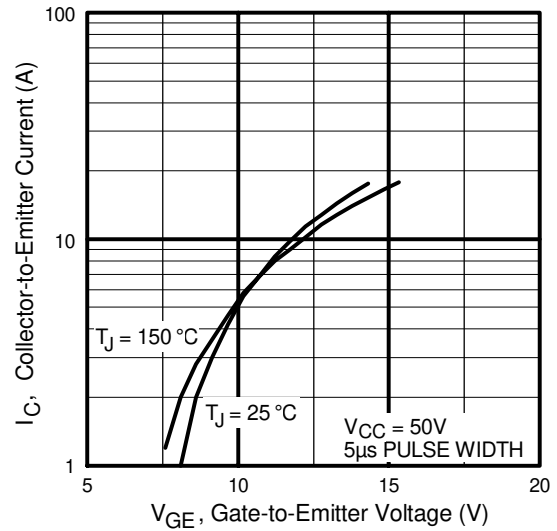


Fig. 3 - Typical Transfer Characteristics

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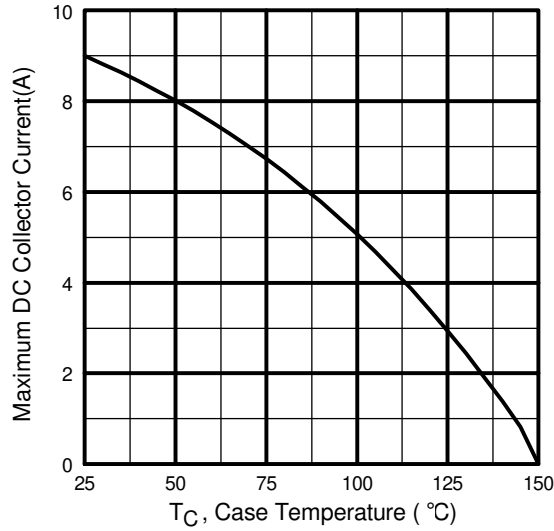


Fig. 4 - Maximum Collector Current vs. Case Temperature

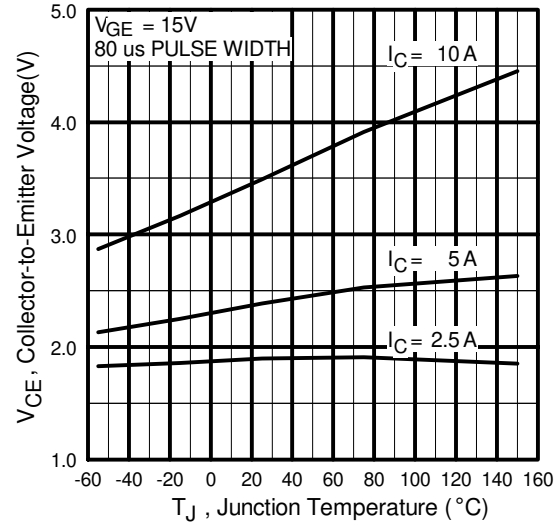


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

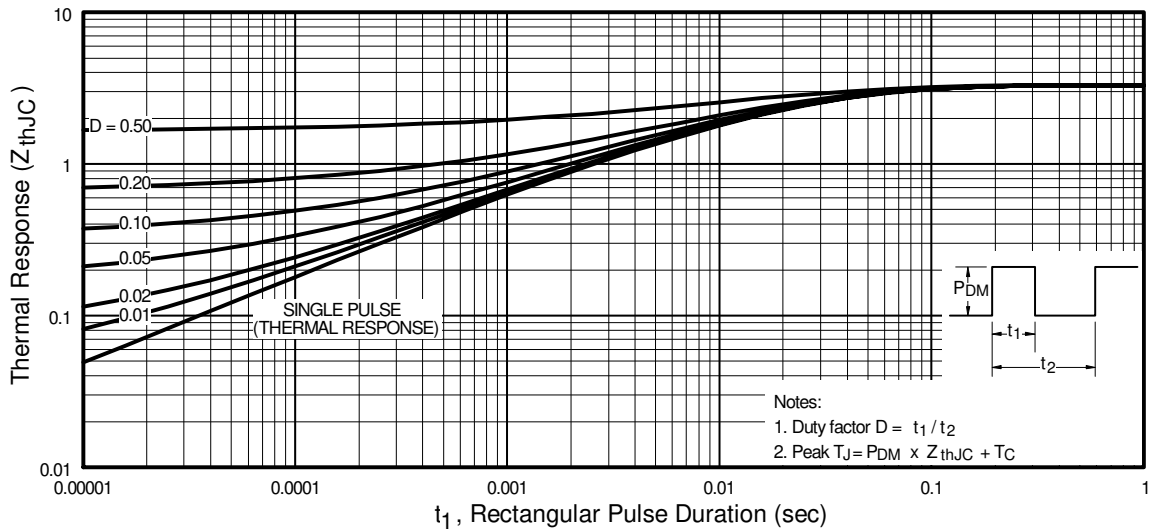


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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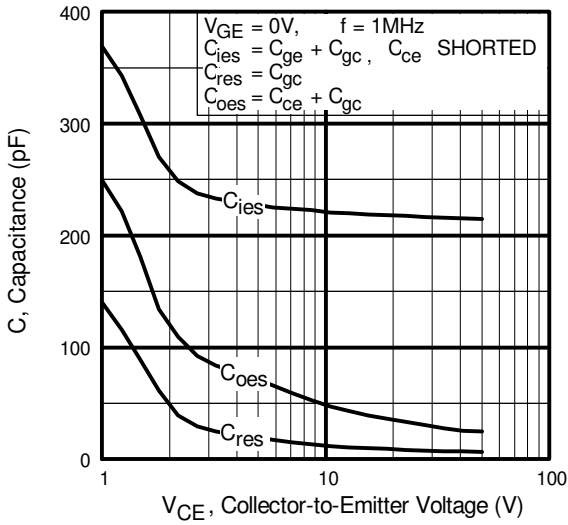


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

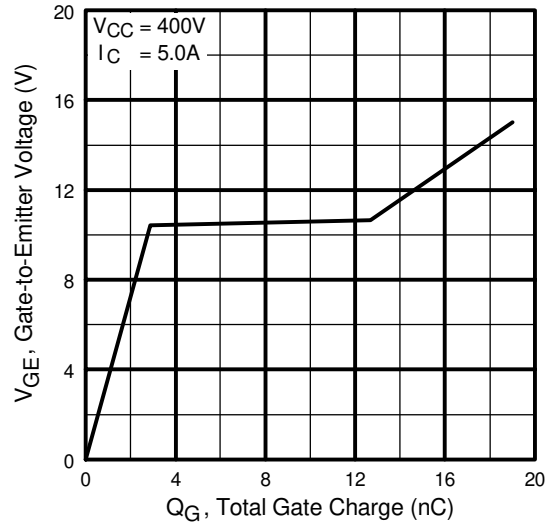


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

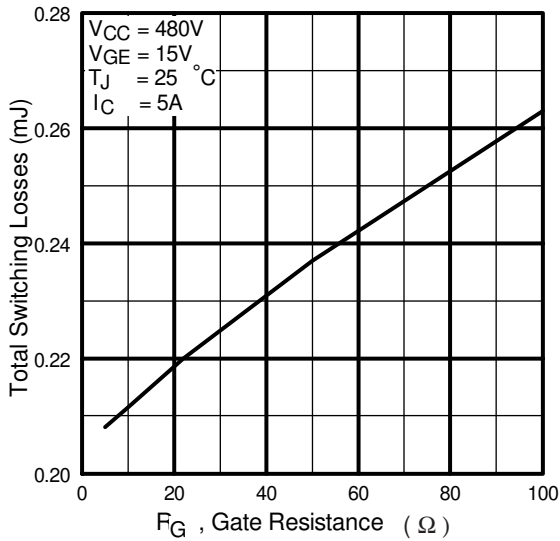


Fig. 9 - Typical Switching Losses vs. Gate Resistance

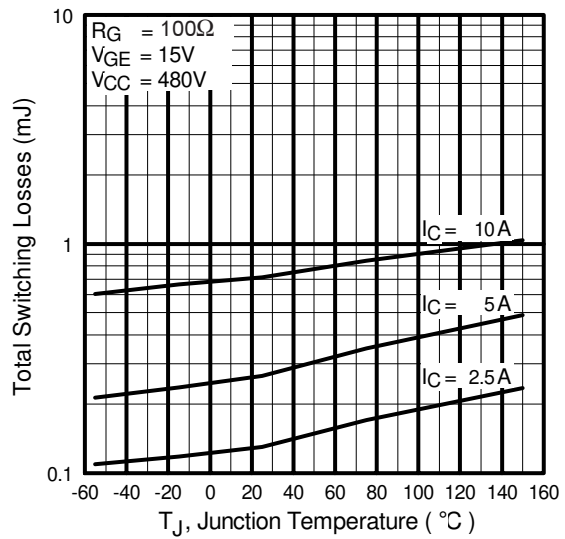


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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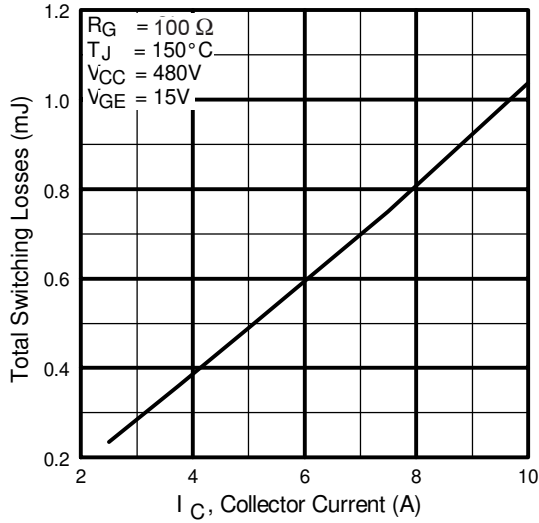


Fig. 11 - Typical Switching Losses vs. Collector Current

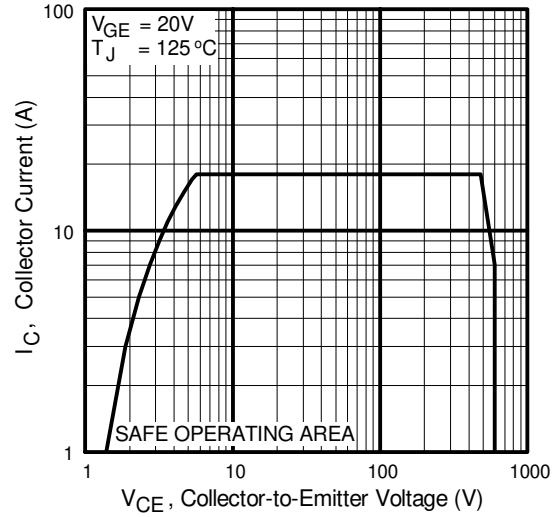


Fig. 12 - Turn-Off SOA

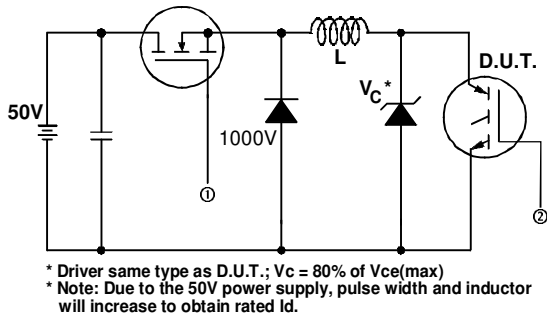


Fig. 13a - Clamped Inductive Load Test Circuit

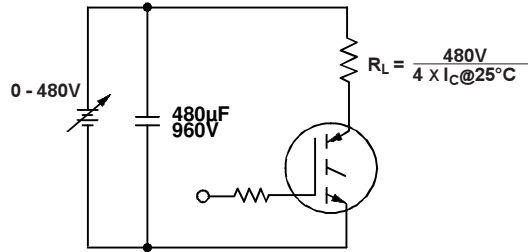


Fig. 13b - Pulsed Collector Current Test Circuit

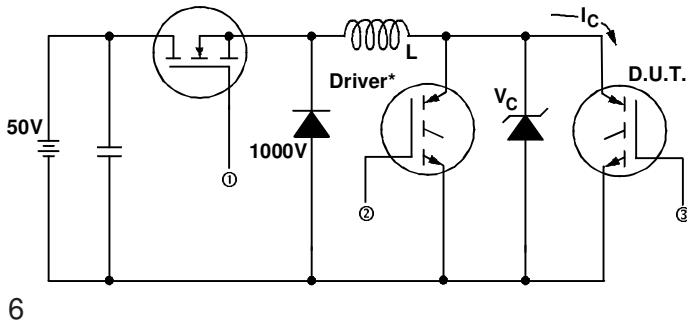


Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., $V_C = 480\text{V}$

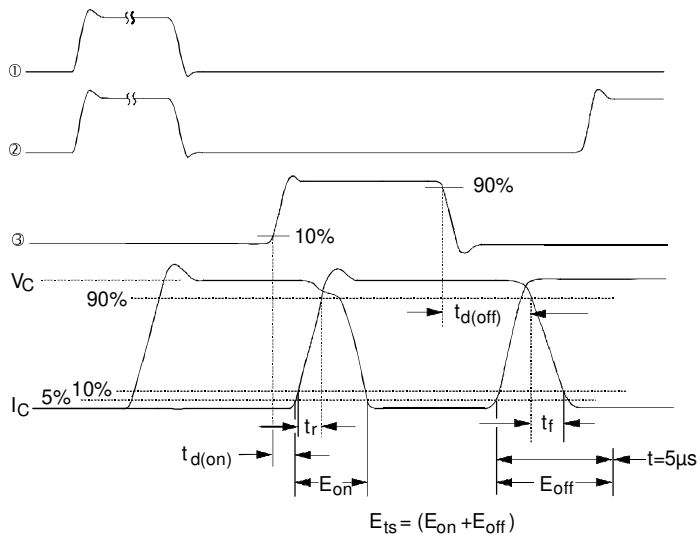
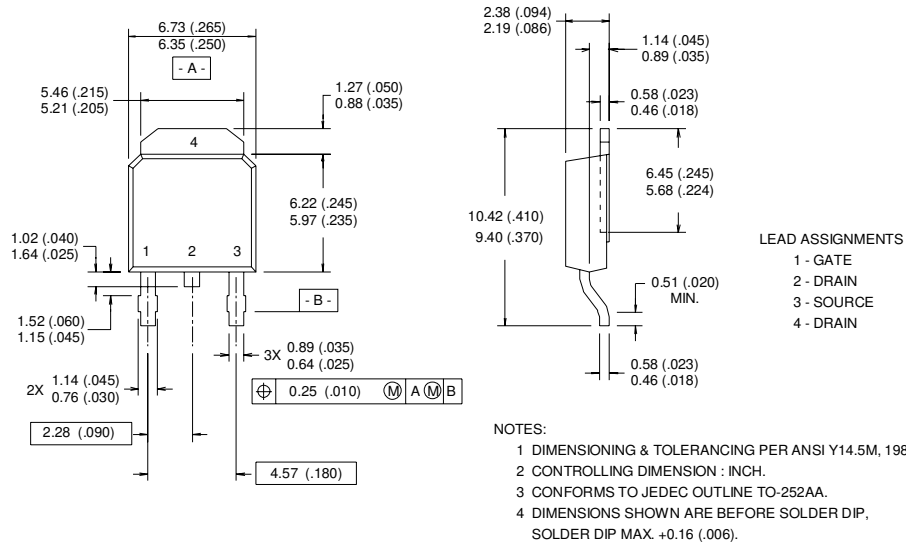


Fig. 14b - Switching Loss Waveforms

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D-Pak (TO-252AA) Package Outline

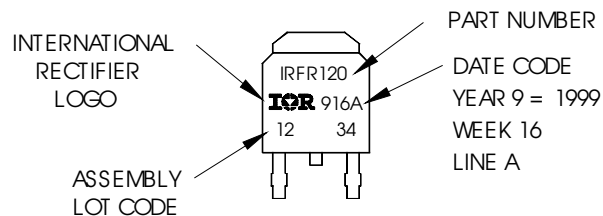
Dimensions are shown in millimeters (inches)



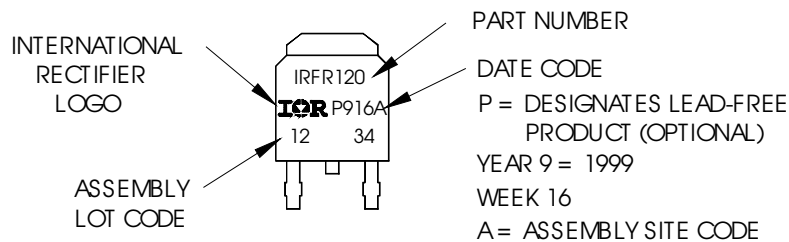
D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line
position indicates "Lead-Free"

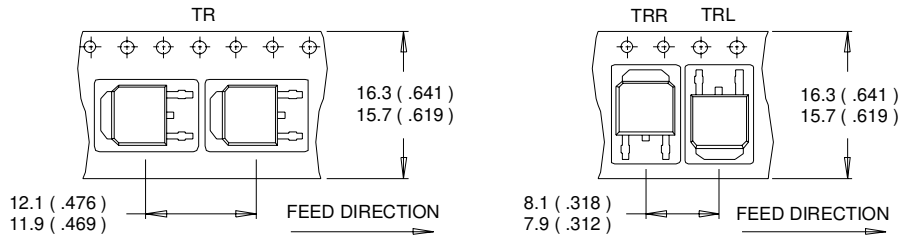


OR



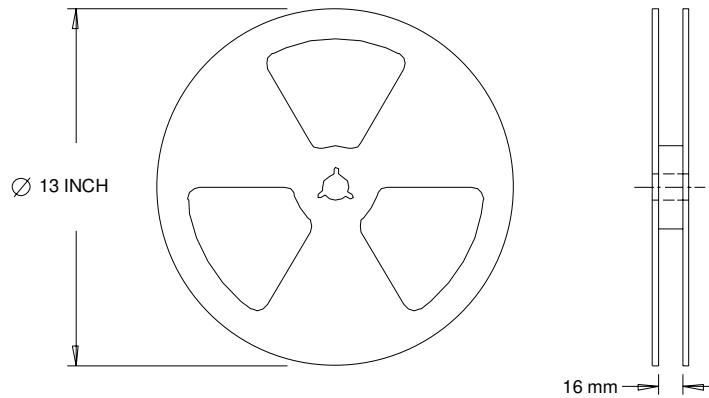
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>